

SM2326NSAN-VB Datasheet

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^e	Q _g (Typ.)			
	0.028 at V _{GS} = 4.5 V	6 ^a				
20	0.042 at V _{GS} = 2.5 V	6 ^a	8.8 nC			
	0.050 at V _{GS} = 1.8 V	5.6				

FEATURES

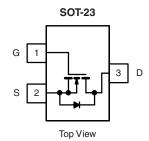
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	± 12	V
	T _C = 25 °C		6 ^a	
Continuous Drain Comment /T 150 °C\	T _C = 70 °C	I _D	5.1	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C		5 ^{b, c}	
	T _A = 70 °C	1	4 ^{b, c}	A
Pulsed Drain Current		I _{DM}	20	
Continuous Source-Drain Diode Current	T _C = 25 °C		1.75	
Continuous Source-Drain Diode Current	T _A = 25 °C	l _S	1.04 ^{b, c}	
	T _C = 25 °C		2.1	
Maximum Bayer Dissination	T _C = 70 °C	P _D	1.3	w
Maximum Power Dissipation	T _A = 25 °C		1.25 ^{b, c}	VV
	T _A = 70 °C	•	0.8 ^{b, c}	
Operating Junction and Storage Temperature	e Range	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Tempera	ature)		260	

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	80	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	60	O/ VV		

Notes:

- a. Package limited
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 125 $^{\circ}\text{C/W}.$
- e. Based on T_C = 25 °C.

服务热线:400-655-8788

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u> </u>		,			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	20			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		25		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.6		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	0.45		1.0	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA
		$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 \text{ °C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	20			Α
		$V_{GS} = 4.5 \text{ V}, I_D = 5.0 \text{ A}$		0.028		Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.7 \text{ A}$		0.042		
		$V_{GS} = 1.8 \text{ V}, I_D = 4.3 \text{ A}$		0.050		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5.0 A		24		S
Dynamic ^b			L		L	
Input Capacitance	C _{iss}			865		pF
Output Capacitance	C _{oss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		105		
Reverse Transfer Capacitance	C _{rss}			55		
· ·		$V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_D = 5.0 \text{ A}$		12	18	
Total Gate Charge	Qg			8.8	14	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 5.0 \text{ A}$		1.1		
Gate-Drain Charge	Q_{gd}			0.7		
Gate Resistance	R_{g}	f = 1 MHz	0.5	2.4	4.8	Ω
Turn-On Delay Time	t _{d(on)}			8	16	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		17	26	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 4$ A, V_{GEN} = 4.5 V, R_g = 1 Ω		31	47	
Fall Time	t _f			8	16	ns
Turn-On Delay Time	t _{d(on)}			5	10	110
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		13	20	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 4 \text{ A}, V_{GEN} = 5 \text{ V}, R_g = 1 \Omega$		21	32	
Fall Time	t _f			6	12	
Drain-Source Body Diode Characteristic	es				L	
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			1.75	
Pulse Diode Forward Current	I _{SM}				20	A
Body Diode Voltage	V_{SD}	I _S = 4 A, V _{GS} = 0 V		0.75	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			12	20	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I 4 A dI/dt 100 A/vo T 05 °C		5	10	nC
Reverse Recovery Fall Time	t _a	$I_F = 4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 \text{ °C}$		7		
Reverse Recovery Rise Time t _b				5		ns

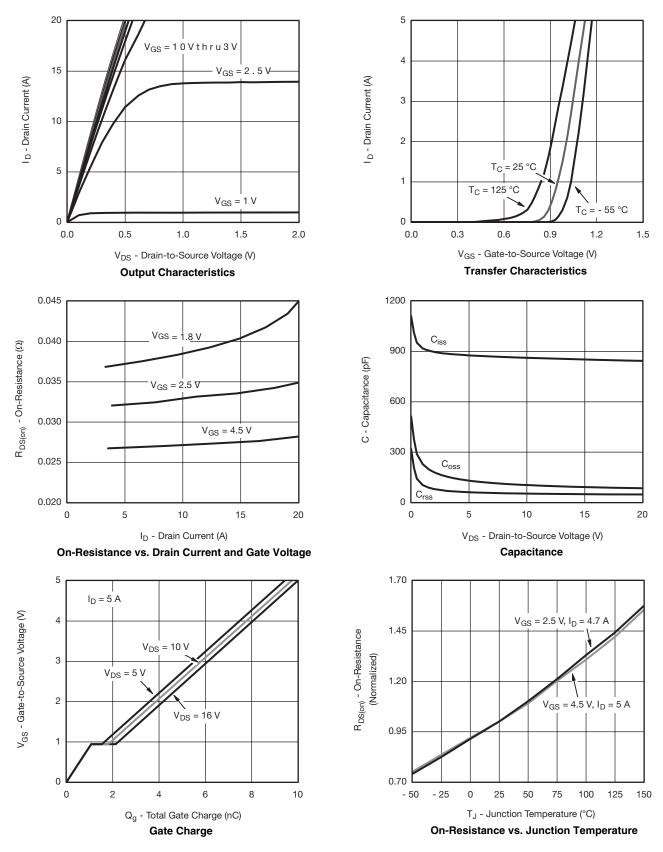
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

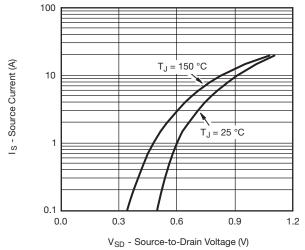


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

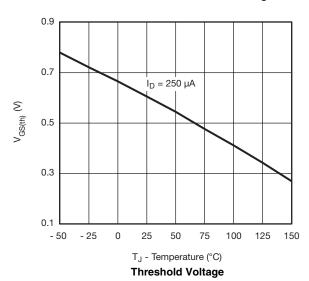


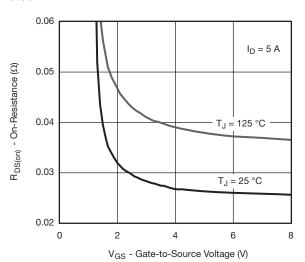


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Source-Drain Diode Forward Voltage

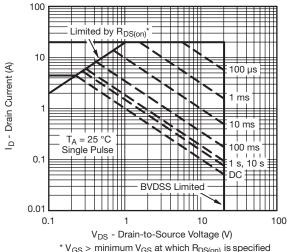




On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power (Junction-to-Ambient)

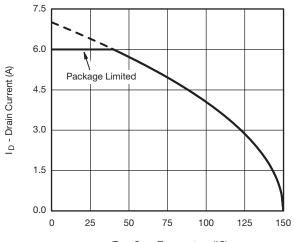


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

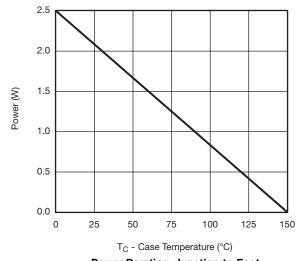


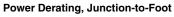
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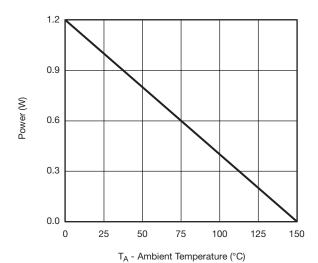


T_C - Case Temperature (°C)

Current Derating*







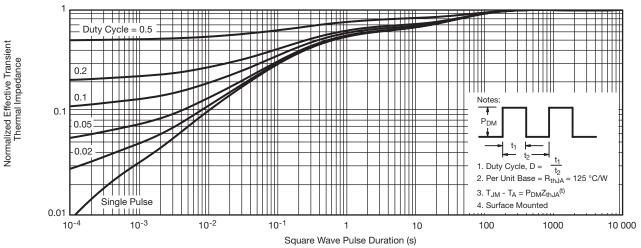
Power Derating, Junction-to-Ambient

^{*} The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

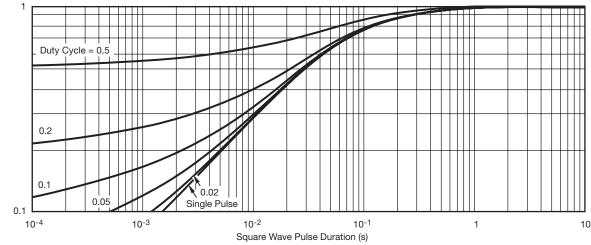
Normalized Effective Transient Thermal Impedance



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



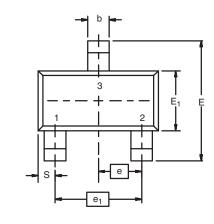
Normalized Thermal Transient Impedance, Junction-to-Ambient

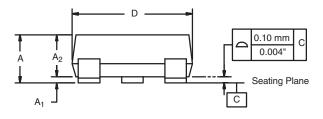


Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K. 09-	Jul-01				

DWG: 5479



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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